

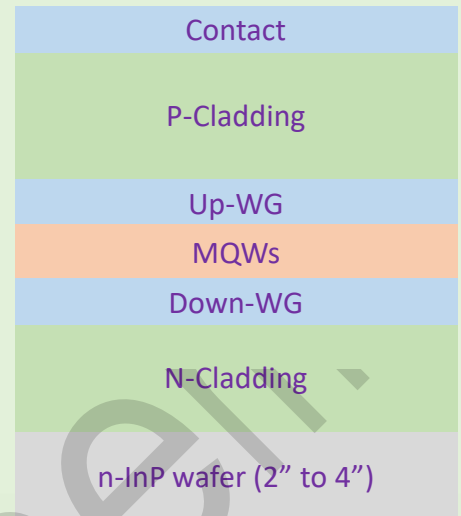
1310 nm FP LD epiwafers



We offer a variety of standard and customized InP based FP LD epiwafers for fiber communications, lidar, sensing, and NIR illumination.

Key Features

- High uniformity PL wavelength (2 inch to 4 inch)
- Special design of high gain MQWs
- Output power up to 5~50 mW (with different device structure)
- High reliability
- Low power consumption
- InGaAsP MQWs or AlGaInAs MQWs available
- Customized lasing wavelength

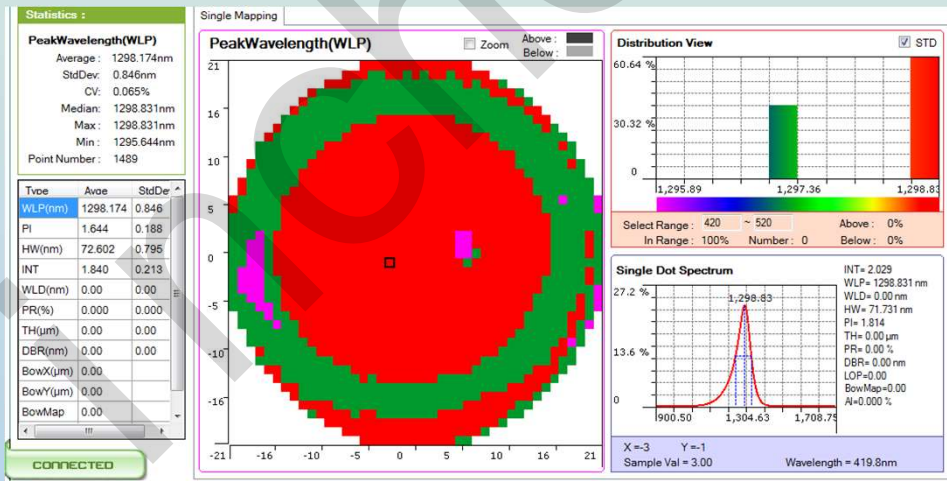


Key Epi-Structure

Default tolerances

Mole fraction	PL (nm)	Thickness (nm)	ECV (cm ⁻³)
±0.05	±10	±5%	±30%

PL Mapping Instance



PIV & Spectrum instance

